Summary

This application note covers the principles of power distribution systems and bypass or decoupling capacitors. A step-by-step process is described where a power distribution system can be designed and verified. The final section discusses additional sources of power supply noise and provides resolutions.

Introduction

FPGA designers are faced with a unique task when it comes to designing power distribution systems (PDS). Most other large, dense ICs (such as large microprocessors) come with very specific bypass capacitor requirements. Since these devices are only designed to implement specific tasks in their hard silicon, their power supply demands are fixed and only fluctuate within a certain range. FPGAs do not share this property. Since FPGAs can implement a practically infinite number of applications at undetermined frequencies and in multiple clock domains, it can be very complicated to predict what their transient current demands will be.

Transient current demands in digital devices are the cause of ground bounce, the bane of high-speed digital designs. In low-noise or high-power situations, the power supply decoupling network must be tailored very closely to these transient current needs, otherwise ground bounce and power supply noise will exceed the limits of the device. The transient currents in an FPGA will be different from design to design. This application note provides an iterative method for designing a bypassing network to suit the individual needs of a specific FPGA design.

The first step in this process is to examine the utilization of the FPGA for its transient current requirements. Next, an approximate decoupling network is designed to fit these requirements. The third step is to refine the network through simulation and modification of capacitor numbers and values. In the fourth step, the full design is built and in the fifth step it is measured. Measurements consist of oscilloscope and possibly spectrum analyzer readings of power supply noise. Depending on the measured results, further iterations through the part selection and simulation steps could be necessary to optimize the PDS for the specific application. A sixth optional step is also given for cases where a perfectly optimized PDS is needed.

Basic Decoupling Network Principles

Before starting into the PDS design flow, it is important to understand the basic electrical principles involved. This section will discuss the purpose of the PDS and the properties of its components.

The purpose of a power distribution system (PDS) is to provide power to the devices in a system. Each of these devices not only has its own wattage requirements for its operation, but also its own requirement for the cleanliness of that power. Most digital devices, including all Virtex families of FPGAs, have a requirement that on all supplies, $V_{CC}$ must not fluctuate more than 5% above or 5% below the nominal $V_{CC}$ value. In this document $V_{CC}$ is used generically to refer to all FPGA power supplies: $V_{CCINT}$, $V_{CCO}$, $V_{CCAUX}$, and $V_{REF}$. This specifies a maximum amount of noise present on the power supply, often referred to as "ripple voltage." If the device requirements state that $V_{CC}$ must be within ±5% of the nominal voltage, that means peak to peak voltage ripple must be no more than 10% of the nominal $V_{CC}$. This assumes that...
nominal $V_{CC}$ is exactly the nominal value given in the datasheet. If this is not the case, then $V_{RIPPLE}$ must accordingly be adjusted to a value less than 10%.

The power consumed by a digital device varies over time, and this variance occurs on all scales. Low frequency variance of power consumption is usually the result of devices or large portions of devices being enabled or disabled. This can occur on time scales from milliseconds to days. High frequency variance of power consumption is the result of individual switching events inside a device, and this happens on the scale of the clock frequency and the first few harmonics of the clock frequency.

Since the voltage level of $V_{CC}$ for a device is fixed, changing power demands are manifested as changing current demand. The PDS must accommodate these variances of current draw with as little impact on power supply voltage as possible.

When the current draw in a device changes, the power distribution system cannot respond to that change instantaneously. For the short time before the PDS responds, the voltage at the device changes. This is where power supply noise appears. There are two main causes for this lag in the PDS corresponding to the two major components of the PDS.

Figure 1 shows the major components of the PDS, the power supply and decoupling capacitors, along with the active device being powered (in this case, an FPGA).

![Simplified PDS Circuit](image1)

**Figure 1: Simplified PDS Circuit**

Figure 2 shows a further simplified PDS circuit, showing all reactive components decomposed to a frequency-dependent resistor.

![Further Simplified PDS Circuit](image2)

**Figure 2: Further Simplified PDS Circuit**

The first major component of the PDS is the voltage regulator. It observes its output voltage and adjusts the amount of current being supplied to keep the voltage constant. Most common voltage regulators make this adjustment on the order of milliseconds to microseconds. They are effective at maintaining output voltage for events at all frequencies from DC to a few hundred kilohertz (depending on the regulator). For all transient events that occur at frequencies above this range, there will be a time lag before the voltage regulator can respond to the new level of demand. For example, if current demand in the device increases in a matter of nanoseconds, the voltage at the device will sag by some amount until the voltage regulator can adjust to the new, higher level of current it must provide.

The second major component of the PDS is the bypass or decoupling capacitors. In this application note, the words “bypass” and “decoupling” are used interchangeably. Their function...
is to act as local energy storage for the device. They cannot provide DC power, as only a small amount of energy is stored (the voltage regulator is present to provide DC power). The function of this local energy storage is to respond very quickly to changing current demands. The capacitors are effective at maintaining power supply voltage at frequencies from hundreds of kilohertz to hundreds of megahertz in the milliseconds to nanoseconds range. Decoupling capacitors are of no use for all events occurring above or below this range. For example, if current demand in the device increases in a few picoseconds, the voltage at the device will sag by some amount until the capacitors can supply extra charge to the device. If current demand in the device changes and maintains this new level for a number of milliseconds, the voltage regulator circuit, operating in parallel with the bypass capacitors, will change its output to supply this new current.

**What is the Role of Inductance?**

There is a property of the capacitors and of the PCB current paths that retards changes in current flow. This is the reason why capacitors cannot respond instantaneously to transient currents, nor to changes that occur at frequencies higher than their effective range. This property is called inductance.

Inductance can be thought of as momentum of charge. Where charge is moving at some rate, this implies some amount of current. If the level of current is to change, the charge must move at a different rate. Because there is momentum (inductance) associated with this charge, it will take some amount of time for the charge to slow down or speed up. The greater the inductance, the greater the resistance to change.

The purpose of the PDS is to accommodate whatever current demands the device(s) could have, and respond to changes in that demand as quickly as possible. When these demands are not met, the voltage across the device's power supply changes. This is observed as noise. Since inductance retards the abilities of bypass capacitors to quickly respond to changing current demands, it should be minimized.

**Figure 1** shows inductances between the device and capacitors, and between the capacitors and the voltage regulator. These inductances arise as parasitics of both the capacitors themselves, and of all current paths in the PCB. It is important that each of these be minimized.

**Capacitor Parasitic Inductance**

Of a capacitor's various properties, the capacitance value is often considered the most important. However in choosing decoupling capacitors, the property of parasitic inductance (ESL or Equivalent Series Inductance) is of the same or greater importance.

The one factor that influences parasitic inductance more than any other is the dimensions of the package. Very simply, physically small capacitors tend to have lower parasitic inductance than physically large capacitors. Just as a short wire has less inductance than a long wire, a short capacitor has less inductance than a long capacitor. Likewise, as a fat or wide wire has less inductance than a narrow wire, so too does a fat capacitor have less inductance than a narrow capacitor.

For these reasons, when choosing decoupling capacitors, the smallest package should be chosen for a given value. Similarly, for a given package size (essentially a fixed inductance value), the highest capacitance value available in that package should be chosen.

Surface-mount chip capacitors are the smallest capacitors available, making them the best choice for discrete bypass capacitors. For values from 2.2 μF down to very small values such as 0.0001 μF, X7R type capacitors are usually used. These have low parasitic inductance, and an acceptable temperature characteristic. For values from 2.2 μF up to very large values such as 1000 μF, tantalum capacitors are used. These have low parasitic inductance and a relatively high equivalent series resistance (ESR), giving them a very wide range of effective frequencies. They also provide a comparatively high capacitance value in a small package size, thus
reducing board real-estate costs. In cases where tantalum capacitors are not available, low-inductance electrolytic capacitors can be used.

A real capacitor has characteristics not only of capacitance but also inductance and resistance. Figure 3 shows the parasitic model of a real capacitor. A real capacitor should be treated as an RLC circuit.

![Parasitics of a Real, Non-Ideal Capacitor](x623_03_072502)

Figure 4 shows the impedance characteristic of a real capacitor. Overlaid on this plot are the curves corresponding to the capacitor's capacitance and parasitic inductance (ESL). These two curves combine to form the total impedance characteristic of the RLC circuit formed by the parasitics of the capacitor.

![Contribution of Parasitics to Total Impedance Characteristics](x623_04_072602)

As capacitive value is increased, the capacitive curve moves down and to the left. As parasitic inductance is decreased, the inductive curve moves down and to the right. Since parasitic inductance for capacitors in a given package is essentially fixed, the inductance curve remains fixed. As different capacitor values are selected in that same package, the capacitive curve moves up and down relative to the fixed inductance curve. The only way to decrease the total impedance of a capacitor if the package is fixed is to increase the value of the capacitor. The only way to move the parasitic inductance curve down (and consequently lower the total impedance characteristic), is to connect additional capacitors in parallel.

**Inductance from PCB Current Paths**

The parasitic inductance of current paths in the PCB have two distinct sources: the capacitor mounting, and the power and ground planes of the PCB.
Mounting Inductance

In this context, the mounting refers to the capacitor’s solder land on the PCB, the trace (if any) between the land and via, and the via itself. Figure 5 shows a variety of mounting geometries.

![Diagram of capacitor mounting geometries](image)

Figure 5: Example Capacitor Land and Mounting Geometries

The existence and/or length of a connecting trace has a big impact on parasitic inductance of the mounting. Wherever possible, there should be no connecting trace (Figure 5a) - the via should butt up against the land itself (Figure 5b). Further improvements can be made to the mounting by placing vias to the side of capacitor lands (Figure 5c), or directly inside the lands themselves (Figure 5e). Currently, very few PCB manufacturing processes allow via-in-pad geometries. Another improvement is to use more than one via per land (Figure 5d). This technique is important when using ultra-low inductance capacitors, such as reverse aspect ratio capacitors (AVXs LICC).

The vias, traces, and pads of a capacitor mounting will contribute anywhere from 300 pH to 4 nH of inductance depending on the specific geometry. Since the inductance of a current path is proportional to the area of the loop the current traverses, it is important to minimize the size of this loop. The loop consists of the path through one power plane, up through one via, through the connecting trace to the land, through the capacitor, through the other land and connecting trace, down through the other via, and into the other plane, as shown in Figure 6.

![Diagram of current loop](image)

Figure 6: Cutaway View of PCB with Capacitor Mounting
By shortening the connecting traces, the area of this loop is minimized and the inductance is reduced. Similarly, by reducing the via length through which the current flows, loop area is minimized and inductance is reduced.

Many times in an effort to squeeze more parts into a small area, PCB layout engineers will opt to share vias among multiple capacitors. **Under no circumstances should this technique be used.** The capacitor mounting (lands, traces and vias) typically contributes about the same amount or more inductance than the capacitor's own parasitic inductance. If a second capacitor is connected into the vias of an existing capacitor, it only improves the PDS by a very small amount. It would be better to reduce the total number of capacitors and maintain a one-to-one ratio of lands to vias.

**Plane Inductance**

The power and ground planes of a PCB have some amount of inductance associated with them. The geometry of these planes determines their inductance.

Since power and ground planes are by definition a planar structure, current does not just flow through them in one direction. It tends to spread out as it travels from one point to another, in accordance with a property similar to skin effect. For this reason, inductance of planes can be described as "spreading inductance," and is specified in units of henries per square. The square is dimensionless, as it is the shape, not the size of a section of plane that will determine its inductance.

Spreading inductance acts like any other inductance — to resist changes to the amount of current in a conductor. In this case, the conductor is the power plane or planes. It is a quantity that should be reduced as much as possible, since it will retard the ability of capacitors to respond to transient currents in the device. Since the X-Y shape of the plane is typically something the designer has little control over, the only controllable factor is the spreading inductance value. This is primarily determined by the thickness of the dielectric separating a power plane and its associated ground plane.

In high-frequency power distribution systems of the type discussed here, power and ground planes work in pairs. Their inductances do not exist independently of each other. The spacing (and to a small extent the dielectric constant of the material) between power and ground planes will determine the spreading inductance of the pair. The closer the spacing, the lower the spreading inductance. **Table 1** gives approximate values of spreading inductance for different thicknesses of FR4 dielectric.

<table>
<thead>
<tr>
<th>Dielectric Thickness (mil, microns)</th>
<th>Inductance (pH/square)</th>
<th>Capacitance (pF/in², pF/cm²)</th>
</tr>
</thead>
<tbody>
<tr>
<td>4, 102</td>
<td>130</td>
<td>225, 35</td>
</tr>
<tr>
<td>2, 51</td>
<td>65</td>
<td>450, 70</td>
</tr>
<tr>
<td>1, 25</td>
<td>32</td>
<td>900, 140</td>
</tr>
</tbody>
</table>

Table 1: Capacitance and Spreading Inductance Values for Various Thicknesses of FR4 Power-Ground Plane Sandwiches (REF 1)

Since closer spacing results in decreased spreading inductance, it is best, wherever possible, to place VCC planes directly adjacent to GND planes in the stackup. Facing VCC and GND planes are sometimes referred to as "sandwiches." While the use of VCC – GND sandwiches was not necessary in the past for previous technologies, the speeds involved and the sheer amount of power required for fast, dense devices demands it.

Besides offering a low-inductance current path, power-ground sandwiches also offer some high-frequency decoupling capacitance. As plane area increases and as the separation between power and ground planes decreases, the value of this capacitance increases. At the same time, since the parasitic inductance of this capacitance is decreasing, its effective
frequency band center frequency increases. Capacitance per square inch is also given in Table 1.

This capacitance alone is usually not enough to give power-ground sandwiches a compelling advantage. However, when viewed as a bonus on top of low spreading inductance, it is an advantage most designers will gladly take.

**Capacitor Effective Frequency**

Every capacitor has a narrow frequency band where it is effective as a decoupling capacitor. Outside this band, it does have some contribution to the PDS but in general it is negligible. The frequency bands of some capacitors are wider than others. The ESR of the capacitor will determine the quality factor (Q) of the capacitor, which determines the width of the effective frequency band. Tantalum capacitors generally have a very wide effective band, while X7R chip capacitors, with their lower ESR, generally have a very narrow effective band.

The effective frequency band corresponds to the capacitor’s resonant frequency. While an ideal capacitor only has a capacitive characteristic, real non-ideal capacitors also have a parasitic inductance ESL and a parasitic resistance ESR. These parasitics act in series to form an RLC circuit (Figure 3). The resonant frequency associated with that RLC circuit is the resonant frequency of the capacitor.

To determine the resonant frequency of the mounted capacitor, the following equation is used:

\[
F = \frac{1}{2\pi\sqrt{LC}}
\]

Equation 1

Alternatively, a frequency sweep SPICE simulation of this capacitor with all its parasitics could be performed, and the frequency where the minimum impedance value occurs would be the resonant frequency.

It is important to distinguish between the capacitor’s self-resonant frequency and the effective resonant frequency of the mounted capacitor when it is part of the system. This is simply the difference between taking into account only the capacitor’s parasitic inductance, and taking into account its parasitic inductance as well as that of the vias, planes, and connecting traces lying between it and the FPGA. The self-resonant frequency of the capacitor \( F_{RSELF} \) (the value reported in the capacitor datasheet), is considerably higher than its effective mounted resonant frequency in the system, \( F_{RIS} \). Since the mounted capacitor's performance is what is important, it is the mounted resonant frequency that is used when choosing a capacitor to eliminate noise at a given frequency.

The main contributors to mounted parasitic inductance are the capacitor’s own parasitic inductance, the inductance of PCB lands and connecting traces, the inductance of vias, and power plane inductance. Vias will traverse a full board stackup on their way to the device when capacitors are mounted on the underside of the board. These vias will contribute something in the range of 300 pH to 1,500 pH on a board with a finished thickness of 60 mils; vias in thicker boards will have higher inductance. Because there are two of these paths in series with each capacitor, twice this value should be added to the capacitor’s parasitic inductance. This quantity, the parasitic inductance of the capacitor mounting, is designated \( L_{MOUNT} \). To determine the total parasitic inductance of the capacitor in-system, \( L_{IS} \), the capacitor’s parasitic inductance \( L_{SELF} \) is added to the parasitic inductance of the mounting:

\[
L_{IS} = L_{SELF} + L_{MOUNT}
\]
Example
X7R Ceramic Chip capacitor (AVX capacitor data used here)

\[ C = 0.01 \, \mu F \]
\[ L_{SELF} = 0.9 \, nH \]
\[ F_{RSELF} = 53 \, MHz \]
\[ L_{MOUNT} = 0.8 \, nH \]

To determine the effective in-system parasitic inductance \( (L_{IS}) \), add the via parasitics:

\[ L_{IS} = L_{SELF} + L_{MOUNT} = 0.9 \, nH + 0.8 \, nH = 1.7 \, nH \]

Plugging in the values from the example:

\[ F_{RIS} = \frac{1}{2\pi \sqrt{L_{IS}C}} \]

\[ F_{RIS} = \frac{1}{2\pi \sqrt{(1.7 \times 10^{-12} \, H) \cdot (1 \times 10^{-8} \, F)}} = 3.8 \times 10^7 \, Hz \]

\( F_{RIS} \): Mounted Capacitor Resonant Frequency: 38 MHz

Since a decoupling capacitor is only effective at a narrow band of frequencies around its resonant frequency, it is important that the resonant frequency be taken into account when choosing a collection of capacitors to build up a decoupling network.

Capacitor Placement

To perform the decoupling function there are two basic reasons why capacitors need to be close to the device.

First, increased spacing between the device and decoupling capacitor will increase the distance travelled by the current in the power and ground planes, and hence, the inductance of the current path between the device and the capacitor. Since the inductance of this path, (the loop followed by current as it goes from the \( V_{CC} \) side of the capacitor to the \( V_{CC} \) pin[s] of the FPGA, and from the GND pin[s] of the FPGA to the GND side of the capacitor[s]), is proportional to the loop area, decreasing its inductance is only a matter of decreasing the loop area. Shortening the distance between the device and the decoupling capacitor(s) reduces the inductance resulting in a less impeded transient current flow. This reason tends to be less important with regard to placement than the second reason.

For a capacitor to be effective in providing transient current at a certain frequency (for instance, the optimum frequency for that capacitor), it must be within a fraction of the wavelength associated with that frequency. Noise from the FPGA falls into certain frequency bands, and different sizes of decoupling capacitors will take care of different frequency bands. For this reason, capacitor placement is determined based on the effective frequency of each capacitor.

When the FPGA initiates a change in its current demand, it will cause a small local disturbance in the voltage of the PDS (in this case, a point in the power and ground planes). For a decoupling capacitor to counteract this, the capacitor has to first see a voltage difference. There is a finite time delay between the start of the disturbance at the FPGA power pins and the start of the capacitor’s view of the disturbance. This time delay is equal to the distance from FPGA power pins to capacitor, divided by the propagation speed of current through FR4 dielectric (the substrate of the PCB where the power planes are embedded). There is another delay of the same duration for the current from the capacitor to reach the FPGA.
Therefore, for any transient current demand in the FPGA, there is a round-trip delay to the capacitor before any relief is seen at the FPGA. For placement distances greater than $\frac{1}{4}$ of a wavelength of some frequency, the energy transferred to the FPGA will be negligible.

For decreasing distances less than a $\frac{1}{4}$ wavelength, the energy transferred to the FPGA increases to 100% at zero distance. Efficient energy transfer from the capacitor to the FPGA requires placement of the capacitor within a fraction of a $\frac{1}{4}$ wavelength of the FPGA power pins. This fraction should be small because the capacitor is also effective at frequencies slightly above its resonant frequency, where the wavelength is shorter.

In practical applications, one tenth of a quarter wavelength is a good target. This leads to placing a capacitor to within one fortieth of a wavelength from the power pins it is decoupling. The wavelength corresponds to $F_{RIS}$, the capacitor's mounted resonant frequency.

**Example**

0.001 $\mu$F X7R Ceramic Chip capacitor, 0402 package

$L_{IS} = 1.6 \text{ nH}$

$F_{RIS} = \frac{1}{2\pi\sqrt{LC}} = \frac{1}{2\pi\sqrt{1.6 \times 10^{-9} \times 0.001 \times 10^{-6}}} = 125.8 \text{MHz}$

Equation 2 calculates $T_{RIS}$, the mounted period of resonance, from $F_{RIS}$

$T_{RIS} = \frac{1}{F_{RIS}} = \frac{1}{125.8 \times 10^6} = 7.95 \text{ ns}$  

Equation 2

Equation 3 computes the wavelength based on $T_{RIS}$ and the propagation velocity in FR4 dielectric.

$\lambda = \text{Wavelength} = \frac{T_{RIS}}{V_{PROP}}$  

where $V_{PROP} = 130 \times 10^{-12} \text{ s/inch}$

$\lambda = \frac{T_{RIS}}{V_{PROP}} = \frac{7.95 \times 10^{-9}}{130 \times 10^{-12}} = 61.2 \text{ inches}$

Equation 3

$R_{PLACE} = \frac{\lambda}{40}$  

Equation 4

$R_{PLACE} = \frac{\lambda}{40} = \frac{61.2 \text{ inches}}{40} = 1.53 \text{ inches}$

In this example, the effective frequency, equal to the resonant frequency, can be determined by Equation 1. This effective frequency is determined to be 125.8 MHz. The reciprocal of this is taken to give the resonant period, 7.95 ns using Equation 2. Using the propagation speed of current in FR4 (approximately 130 ps per inch), the wavelength associated with this capacitor is computed to be approximately 61 inches using Equation 3. As computed in Equation 4, one fortieth of this is 1.53 inches. Therefore the target placement radius ($R_{PLACE}$) for capacitors of this size is within 1.53 inches (3.8 cm) of the power and ground pins they are decoupling.
All other capacitor sizes follow in the same manner. A radius of 1.53 inches is not terribly difficult to achieve in current PCB technology. It does not require placing capacitors directly underneath the device on the opposite side of the PCB. It is acceptable for capacitors to be mounted around the periphery of the device, provided the target radius is maintained. The 0.001 \( \mu \text{F} \) capacitors are usually among the smallest in the decoupling network, so placement radii are rarely smaller than an inch. For larger capacitors, the target placement radius expands quickly as the resonant frequency goes down. A 4.7 \( \mu \text{F} \) capacitor, for example, can be placed anywhere on the board, as its target radius of 123 inches is much bigger than most PCBs (corresponding to the resonant frequency of 1.56 MHz).

PDS Design and Verification

Having discussed the basic operating principles of power distribution systems, this section introduces a step-by-step process for designing and verifying a PDS.

**Step 1: Determining Critical Parameters of the FPGA**

In designing the first iteration of the decoupling capacitor network, the basic objective is to have one capacitor per \( V_{CC} \) pin used on the device. Therefore, the *effective* number of \( V_{CC} \) pins for each supply must be determined.

Very few designs use 100% of the various resources in the FPGA. The FPGA package and the PDS inside it are very carefully sized to meet the needs of a fully utilized die without being overly conservative. The number of \( V_{CC} \) and GND pins on a package for a given device is determined based on the needs of a 100% utilized FPGA. The determining factor is not DC power handling abilities — it is transient current impedance. Decoupling capacitor requirements track very closely since they are based on the same factor. For this reason, the number of \( V_{CC} \) pins on each supply is used as an indicator of the number of capacitors needed on that supply. All supplies must be considered: \( V_{CCINT} \), \( V_{CCAUX} \), \( V_{CCO} \), and \( V_{REF} \).

It is only necessary to provide one capacitor per \( V_{CC} \) pin if all pins are used. There is no need to decouple \( V_{REF} \) pins if they are not used as \( V_{REF} \). Conversely, \( V_{CCAUX} \) and \( V_{CCINT} \) pins must always be fully decoupled, i.e., they must always have one capacitor per pin. \( V_{CCO} \) can be pro-rated according to I/O utilization.

**Pro-rating \( V_{CCO} \) pins**

The number of \( V_{CCO} \) pins used by a device can be determined based on the Simultaneously Switching Output (SSO) restrictions given in the device documentation (data sheet and user guide). A budget is calculated on a per-bank basis using these restrictions. The utilization of I/O resources in a bank determines the percentage of the budget used. This percentage represents the percentage of \( V_{CCO} \) pins used by the device.

**Example: Using an XC2V3000 FF1152**

**Single Bank Example**

In a hypothetical design, Bank 0 has 80 outputs in it. Each is configured as a 3.3V LVCMOS 12 mA Fast driver.

The limit for 3.3V LVCMOS 12 mA Fast drivers in the SSO table of the datasheet is 10 per \( V_{CC}/\text{GND} \) pair. There are 13 \( V_{CCO} \) pins per bank on this device. Therefore, the limit for this type of I/O driver is 130 per bank.

This bank uses 80 outputs. Therefore the percentage of the total bank 0 budget that is used is:

\[
\text{Bank 0 Percentage Used} = \frac{\text{Used}}{\text{Limit}} = \frac{80}{130} = 62\%
\]
**Full Device Example**

In this example, the utilization of all I/Os for one device is listed in Table 2, as well as the per-bank SSO limits for each standard (Table 3), computed from the number per $V_{CC}/GND$ pair SSO limits in the Virtex-II User Guide.

**Table 2: I/O Utilization for Each Bank in Full Device Example**

<table>
<thead>
<tr>
<th>Bank Number</th>
<th>Voltage</th>
<th>I/O Utilization</th>
<th>I/O Standard</th>
</tr>
</thead>
<tbody>
<tr>
<td>Bank 0</td>
<td>3.3V</td>
<td>80</td>
<td>LVCMOS_12F</td>
</tr>
<tr>
<td>Bank 7</td>
<td>3.3V</td>
<td>80</td>
<td>LVCMOS_12F</td>
</tr>
<tr>
<td>Bank 1</td>
<td>1.5V</td>
<td>16</td>
<td>LVDCI</td>
</tr>
<tr>
<td>Bank 6</td>
<td>1.5V</td>
<td>16</td>
<td>LVDCI</td>
</tr>
<tr>
<td>Bank 2</td>
<td>1.8V</td>
<td>32</td>
<td>HSTL_1</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>45</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>LVCMOS_12F</td>
</tr>
<tr>
<td>Bank 3</td>
<td>1.8V</td>
<td>32</td>
<td>HSTL_1</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>45</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>LVCMOS_12F</td>
</tr>
<tr>
<td>Bank 4</td>
<td>1.8V</td>
<td>32</td>
<td>HSTL_1</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>45</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>LVCMOS_12F</td>
</tr>
<tr>
<td>Bank 5</td>
<td>1.8V</td>
<td>32</td>
<td>HSTL_1</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>45</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>LVCMOS_12F</td>
</tr>
</tbody>
</table>

**Table 3: SSO Limits for I/O Standards of Full Device Example**

<table>
<thead>
<tr>
<th>I/O Standard</th>
<th>SSO Limit Per Bank</th>
</tr>
</thead>
<tbody>
<tr>
<td>3.3V LVCMOS_12F</td>
<td>130</td>
</tr>
<tr>
<td>1.5V LVDCI</td>
<td>130</td>
</tr>
<tr>
<td>1.8V HSTL_1</td>
<td>260</td>
</tr>
<tr>
<td>1.8V LVCMOS_12F</td>
<td>117</td>
</tr>
</tbody>
</table>
The budget for banks 0, 7, 1, and 6 are computed as in the single-bank example. Banks 2, 3, 4, and 5, however, all have two I/O standards in them. For these banks, the budget is computed for each standard separately, and then the two are combined.

For Banks 2, 3, 4, and 5:

1.8V HSTL_1:
\[
\text{\% used} = \frac{\text{used}}{\text{limit}} = \frac{32}{260} = 13\%
\]

1.8V LVCMOS_12F:
\[
\text{\% used} = \frac{\text{used}}{\text{limit}} = \frac{45}{117} = 39\%
\]

Total budget for each bank:
\[
13\% + 39\% = 52\%
\]

Table 4 summaries the budgets for each bank of the device.

<table>
<thead>
<tr>
<th>Bank Number</th>
<th>Budget</th>
</tr>
</thead>
<tbody>
<tr>
<td>Bank 0</td>
<td>62%</td>
</tr>
<tr>
<td>Bank 7</td>
<td>62%</td>
</tr>
<tr>
<td>Bank 1</td>
<td>12%</td>
</tr>
<tr>
<td>Bank 6</td>
<td>12%</td>
</tr>
<tr>
<td>Bank 2</td>
<td>52%</td>
</tr>
<tr>
<td>Bank 3</td>
<td>52%</td>
</tr>
<tr>
<td>Bank 4</td>
<td>52%</td>
</tr>
<tr>
<td>Bank 5</td>
<td>52%</td>
</tr>
</tbody>
</table>

The number of \(V_{CCO}\) pins used in a bank (Table 5) is simply the number of \(V_{CCO}\) pins in a bank times the percentage of the SSO budget used.

Table 5: Number of \(V_{CCO}\) Pins Used

<table>
<thead>
<tr>
<th>Bank Number</th>
<th>Calculated</th>
<th>Number of Pins Used</th>
</tr>
</thead>
<tbody>
<tr>
<td>Bank 0</td>
<td>13 pins (\times 62%)</td>
<td>8 pins</td>
</tr>
<tr>
<td>Bank 7</td>
<td>13 pins (\times 62%)</td>
<td>8 pins</td>
</tr>
<tr>
<td>Bank 1</td>
<td>13 pins (\times 12%)</td>
<td>2 pins</td>
</tr>
<tr>
<td>Bank 6</td>
<td>13 pins (\times 12%)</td>
<td>2 pins</td>
</tr>
<tr>
<td>Bank 2</td>
<td>13 pins (\times 52%)</td>
<td>7 pins</td>
</tr>
<tr>
<td>Bank 3</td>
<td>13 pins (\times 52%)</td>
<td>7 pins</td>
</tr>
<tr>
<td>Bank 4</td>
<td>13 pins (\times 52%)</td>
<td>7 pins</td>
</tr>
<tr>
<td>Bank 5</td>
<td>13 pins (\times 52%)</td>
<td>7 pins</td>
</tr>
</tbody>
</table>
Step 2: Designing the Generic Bypassing Network

A number of Xilinx test boards and customer designs were analyzed to discern some trends of successful PDS designs. In 80% to 100% utilized designs with power supply noise on the order of half the maximum allowed power supply noise ($V_{RIPPLE}/2$), the PDS generally has approximately one capacitor per $V_{CC}$ pin on a per-supply basis. The generic bypassing network is designed with this range of capacitors in mind. The pro-rated number of power supply pins is used.

Given the number of discrete capacitors needed, a distribution of capacitor values adding up to that total number must be determined. To cover a broad range of frequencies, a broad range of capacitor values must be used. The proportion of high-frequency capacitors to low-frequency capacitors is an important factor.

The objective of a parallel combination of a number of values of capacitors is to keep a low and flat power supply impedance over frequencies from the 500 kHz range to the 500 MHz range. Both large value (low frequency) and small value (high frequency) capacitors are needed. Small value capacitors tend to have less of an impact on the total impedance profile, so a greater number of small value capacitors than large value capacitors are needed.

To keep the impedance profile smooth and free of anti-resonance spikes, a capacitor is generally needed at least in every decade of the capacitor value range. The typical ceramic capacitor range generally spans values from 0.001 μF to 4.7 μF. The exact value of these capacitors is not critical. What is critical is having some capacitor in every order of magnitude over this range.

A ratio of capacitors giving a relatively flat impedance is one where the number of capacitors is roughly doubled for every decade of decrease in size. In other words, if the bottom three values in the network were 0.1 μF, 0.01 μF and 0.001 μF, the network might have two 0.1 μF capacitor, four 0.01 μF capacitors, and eight 0.001 μF capacitors.

In addition, low-frequency capacitance in the form of tantalum, OS-CON, or electrolytic capacitors is needed. These large capacitors typically have a higher ESR than ceramic chip capacitors, making them effective over a wider range of frequencies. For this reason, it is not necessary to maintain the rule of one value per decade. Generally, one value in the 470 μF to 1000 μF range is sufficient.

A set of percentages is helpful for calculating these ratios based on the total number of capacitors (Table 6).

Table 6: Capacitor Value Percentages for a Balanced Decoupling Network

<table>
<thead>
<tr>
<th>Capacitor Value</th>
<th>Quantity Percentage</th>
</tr>
</thead>
<tbody>
<tr>
<td>470 μF to 1000 μF</td>
<td>3%</td>
</tr>
<tr>
<td>1.0 to 4.7 μF</td>
<td>6%</td>
</tr>
<tr>
<td>0.1 to 0.47 μF</td>
<td>16%</td>
</tr>
<tr>
<td>0.01 to 0.047 μF</td>
<td>25%</td>
</tr>
<tr>
<td>0.001 to 0.0047 μF</td>
<td>50%</td>
</tr>
</tbody>
</table>

For every power supply except $V_{RIPPLE}$, this ratio should be maintained. For $V_{RIPPLE}$ supplies, the values should be distributed in a 50/50 ratio of 0.1 μF capacitors and 0.01 μF capacitors. Since the primary function of $V_{RIPPLE}$ decoupling capacitors is reduce the impedance of $V_{RIPPLE}$ nodes to reduce crosstalk coupling, very little low-frequency energy is needed. Therefore, only capacitors in the 0.1 μF - 0.01 μF range are necessary.
1.5V Supply Example

In this example, the 1.5V supply for the Virtex-II device supplies V_CCO for banks 1 and 6, and V_CClnt. There are 44 V_CClnt pins on this device. Banks 1 and 6 were previously calculated to use two pins each. Adding the 44 V_CClnt pins and the four V_CCO pins for Banks 1 and 6 equals 48 pins. Therefore, there should be 48 capacitors on the 1.5V supply. Table 7 shows how the quantity of each value of capacitor is determined.

Table 7: Calculation of Capacitor Quantities for 1.5V Supply Example

<table>
<thead>
<tr>
<th>Capacitor Value</th>
<th>Calculated</th>
<th>Quantity of Capacitors</th>
</tr>
</thead>
<tbody>
<tr>
<td>680 µF</td>
<td>48 pins x 3% = 0.44</td>
<td>1</td>
</tr>
<tr>
<td>2.2 µF</td>
<td>48 pins x 6% = 2.88</td>
<td>3</td>
</tr>
<tr>
<td>0.47 µF</td>
<td>48 pins x 15% = 7.68</td>
<td>8</td>
</tr>
<tr>
<td>0.047 µF</td>
<td>48 pins x 25% = 12</td>
<td>12</td>
</tr>
<tr>
<td>0.0047 µF</td>
<td>48 pins x 50% = 24</td>
<td>24</td>
</tr>
</tbody>
</table>

This calculation gives a first-pass estimate of the capacitors necessary for the 1.5V supply. Changes can be made to the exact number of capacitors to accommodate different values and to make the supply more symmetric (e.g., using four 2.2 µF capacitors instead of three for a more standard the PCB layout). Capacitor values can also be modified according to the specific constraints of the design (e.g., a pre-existing BOM of capacitors). This process of capacitor selection must be repeated for each supply.

Step 3: Simulation

During simulation, the generic decoupling network is verified and in some cases refined. The designer can experiment with different values of capacitors or different packages to achieve an optimum power supply impedance profile.

The simulation circuit is essentially a parallel combination of the decoupling capacitors with associated parasitics. The simulator calculates the aggregate impedance over the pertinent range of frequencies. A number of PDS design tools available from various EDA vendors are listed in Appendix D: EDA tools for PDS Design and Simulation. The equivalent circuit can also be created and analyzed in SPICE (see Appendix C: SPICE Simulation Examples for example SPICE deck). Plotting of the impedance profile can be performed in a spreadsheet tool (e.g., Microsoft Excel).

In using these tools to simulate a bypassing network, it is important to have accurate parasitic values. Obtaining accurate parasitic data from the capacitor vendor or from in-house testing is important. The mounting parasitics lying in the path between the bypass capacitor and the FPGA need to be taken into account. These parasitics combined in series give the mounted capacitor parasitic resistance and inductance. The section on Mounting Inductance covers the details of mounting modeling. Appendix B: Calculation of Via Inductance lists equations for via parasitic inductance. For the following simulation, a value of 0.8 nH to 0.9 nH was added to each of the capacitors’ parasitic self-inductance to come up with L_{IS}. This reflects the inductance of small capacitor mountings in a board on the order of 60 mils thick. Thicker board stackups will have a higher associated via inductance.

Figure 7 shows an impedance plot from a simulation of the parallel combination of these capacitors, taking into account their parasitics and the approximate parasitics of the PCB. An equivalent SPICE netlist is included in Appendix C: SPICE Simulation Examples. Table 8 lists the capacitor quantities, values, and parasitic values used in the simulation.
This collection of capacitors is a good start. The impedance is below 0.03 Ω from 500 KHz to 150 MHz, and increases to 0.07 Ω at 500 KHz. Over this range there are no significant anti-resonance spikes. These capacitors will be used in the board design.

**Step 4: Building the Design**

At this stage, the PCB is laid out with the final capacitor networks verified in simulation. The board is built and tested.

**Step 5: Measuring Performance**

In the performance measurement step, measurements are made to determine whether the PDS is adequate for the devices it is serving. Determining whether or not a bypassing network is adequate for a given design is relatively simple. The measurement is performed with a high-
bandwidth oscilloscope (1 GHz oscilloscope and 1 GHz probe at minimum), on a design running realistic test patterns.

**Noise Magnitude Measurement**

The measurement is taken either directly at the power pins of the device, or across a pair of unused I/O, one driven High and one driven Low. The best measurement technique to measure power supply noise directly at the power pins is by probing their vias on the back side of the PCB.

When making the noise measurement at the back-side of the board, it is necessary to take into account the parasitics of the vias in the path between the measuring point and FPGA, as any voltage drop occurring in this path will not be accounted for in the oscilloscope measurement.

When measuring $V_{CCO}$ noise, the measurement can be taken at a pair of I/O pins configured as strong drivers to logic 1 and logic 0. This technique, when performed correctly, can also show die-level noise.

To make these measurements, the oscilloscope should be in infinite persistence mode, to acquire noise over a long time period (many seconds or minutes). If the design operates in a number of different modes, utilizing different resources in different amounts, these various conditions and modes should be in operation while the oscilloscope is acquiring the noise measurement. Noise measurements should be made at a few different $V_{CC}/GND$ pairs on the FPGA to eliminate the effects of a local noise phenomena.

Figure 8 shows an instantaneous noise measurement taken at the $V_{CCINT}$ pins of a sample design. Figure 9 shows an infinite persistence noise measurement of the same design. Since the infinite persistence measurement will catch ALL noise events over a long period, it will obviously yield more accurate results.

*Figure 8: Instantaneous Measurement of $V_{CCO}$ Supply, with Multiple I/O Sending Patterns at 100 MHz*
This measurement represents the peak-to-peak noise. If it is greater than or equal to the maximum $V_{CC}$ ripple voltage specified in the datasheet (10% of $V_{CC}$), then the bypassing network is not adequate. The maximum voltage ripple allowed for this particular supply, with a nominal value of 1.5V DC, is 10% of this, or 150mV. The scope shots show noise in the range of 60 mV. From this measurement, it is clear that the decoupling network is adequate.

If, however, the measurement showed noise greater than 10% of $V_{CC}$, the PDS would be inadequate. To have a working, robust design, changes should be made to the PDS. A greater number of capacitors, different capacitance values, or different numbers of the various decoupling capacitor values will bring the noise down.

Having the necessary information to improve the decoupling network requires additional measurements. Specifically, measurement of the noise power spectrum could be necessary to determine the frequencies where the noise resides. Excessive noise at a certain frequency indicates a frequency where the PDS impedance is too high for the transient current demands of the device. Armed with this information, the designer can modify the PDS to accommodate the transient current at the specific frequency. This is usually accomplished by adding capacitors with resonant frequencies close to the frequency of the noise.

Noise Spectrum Measurements

A spectrum analyzer is a frequency-domain instrument. It shows the frequency content of a voltage signal at its inputs. When used to measure an inadequate PDS, the user can see the exact frequencies where the PDS is inadequate. Excessive noise at a certain frequency indicates a frequency where the PDS impedance is too high for the transient current demands of the device. Armed with this information, the designer can modify the PDS to accommodate the transient current at the specific frequency. This is usually accomplished by adding capacitors with resonant frequencies close to the frequency of the noise.

The noise spectrum measurement should be taken in the same place as the peak-to-peak noise measurement — directly underneath the device, or at a pair of unused I/O driven High and Low. A spectrum analyzer takes its measurements through a 50 Ω cable, rather than through an active probe like the oscilloscope. One of the best ways to attach the cable for measurements is through an SMA connector tapped into the power and ground planes in the...
vicinity of the device. In most cases this is not available. Another way to attach the cable for measurement of noise in the power planes is to remove a decoupling capacitor in the vicinity of the device, solder the center conductor and shield of the cable directly to the capacitor lands. Alternatively, a probe station can be used.

In most cases, what will be seen are distinct bands of noise at fixed frequencies. These correspond to the clock frequency and its harmonics. The height of each band represents its relative power. The majority of the energy is usually contained in tight bands around 3 or 4 of the harmonics, with power falling off as frequency increases.

Figure 10 shows an example of a noise spectrum measurement. It is a screenshot of a spectrum analyzer measurement of power supply noise on $V_{CCO}$, with multiple I/O sending patterns at 150 MHz.

![Figure 10: Screenshot of Spectrum Analyzer Measurement of $V_{CCO}$](image)

The noise bands correspond to frequencies where the FPGA has a demand for current but is not receiving it from the capacitors. This could be because there is not enough capacitance, or because there is enough capacitance but the parasitic inductance of the path separating the capacitors from the FPGA is too great. In either case, the impedance of the power supply at this frequency is too high. Conversely, at frequencies where there is very little or no noise the impedance can be lower than it needs to be. To solve these problems, the bypassing network must be modified. New capacitor values, or different quantities of the original values should be chosen.

**Step 6: Optimum Bypassing Network Design (Optional)**

In cases where a highly optimized PDS is needed, further measurements can be taken to guide the design of a carefully tailored decoupling network. A network analyzer can be used to measure the impedance profile of a prototype PDS, giving an output similar to what was discussed in the simulation section. The network analyzer will sweep a stimulus across a range of frequencies, and measure the impedance of the PDS at each frequency. Its output is impedance as a function of frequency.
Since the spectrum analyzer gives an output of voltage as a function of frequency, these two measurements can be used together to determine transient current as a function of frequency.

\[ I(f) = \frac{V(f) \text{ From Spectrum Analyzer}}{Z(f) \text{ From Network Analyzer}} \]

Armed with an understanding of the designs transient current requirements, the designer can make further calculations. With maximum voltage ripple value from the datasheet, the value of impedance needed at all frequencies can be determined. This yields a target impedance as a function of frequency. Given this, a network of capacitors can be designed to accommodate the transient current of the specific design. This six-step process lays out a closed-loop method for designing and verifying a power distribution system. Its use ensures an adequate PDS for any design.

If this step-by-step method does not yield a design meeting the required noise specifications, then other aspects of the system should be analyzed for possible changes.

**Possibility 1: Excessive Noise from Other Devices on Board**

When ground and/or power planes are shared among many devices, as is often the case, noise from an inadequately decoupled device can affect the PDS at other devices. RAM interfaces with inherently high transient current demands due to temporary periodic contention are a common cause; large microprocessors are another. If unacceptable amounts of noise are measured locally at these devices, an analysis should be done on the local PDS and decoupling networks of the component.

**Possibility 2: Parasitic Inductance of Planes, Vias, or Connecting Traces**

In this case there is enough capacitance in the bypassing network, but too much inductance in the path from the capacitors to the FPGA. This could be due to a bad choice of connecting trace or solder land geometry, too long a path from capacitors to the FPGA, and/or power vias that traverse an exceptionally thick stackup.

In the case of inadequate connecting trace and capacitor land geometry, it is important to keep in mind the loop inductance of the current path. If the vias for a bypass capacitor are spaced a few millimeters from the capacitor solder lands on the board, the current loop area is greater than it needs to be (Figure 5a). Vias should be placed directly against capacitor solder lands (Figure 5b). Never connect vias to the lands with a short section of trace (Figure 5a). Other improvements of geometry are via-in-pad (where the via is actually under the solder land), shown in Figure 5e, and via beside pad (where vias are not at the ends of the lands, but rather astride them), see Figure 5c. Double vias are another improvement (Figure 5d).

If the inductance of the path in the planes is too great, there are two parameters that can be changed; the length of the electrical path, and the spreading inductance of the planes themselves.

The path length is determined by capacitor placement. Capacitors must be placed close to the power/ground pin pairs on the device being bypassed. This is especially important for the smallest capacitors in the network, since care has been taken to chose capacitors with low parasitic inductance. There is no reason to connect a low inductance, high-frequency capacitor to a device through a high-inductance path. Larger capacitors inherently have a high parasitic self inductance allowing the proximity to the device to be less important.

The spreading inductance of the planes is controlled by the plane spacing and by the dielectric constant of the material between them. See section on “Plane Inductance”.

When boards are exceptionally thick (greater than 100 mils or 2.5 mm), vias have higher parasitic inductance. In these cases, the following changes to the design should be considered.
The first is to move the $V_{CC}/GND$ plane sandwiches close to the top surface the FPGA is on. The second is to place the highest frequency capacitors on the top surface. Both changes together will reduce the parasitic inductance of long vias.

**Possibility 3: I/O Signals in PCB are Stronger Than Necessary**

If noise in the $V_{CCO}$ PDS is still too high after making refinements to the PDS, the I/O interface power can be scaled back. This goes for both outputs from the FPGA and inputs to the FPGA. In some cases, excessive overshoot on inputs to the FPGA can reverse-bias the clamp diodes in the IOBs. This can put large amounts of noise into $V_{CCO}$. If this condition is occurring, the drive strength of these interfaces should be decreased, or termination should be used (both on input and output paths).

**Possibility 4: I/O Signal Return Current Travelling in Sub-Optimal Paths**

Excessive noise in the PDS can be caused by I/O signal return currents. For every signal transmitted by a device into the PCB (and eventually into another device), there is an equal and opposite current flowing from the PCB back into the device’s power/ground system. If there is no low-impedance return current path available, a less optimal, higher impedance path will be used. When this occurs, voltage changes are induced in the PDS.

This situation can be improved by ensuring that every signal has a closely spaced and fully intact return path. Various strategies could be required including restricting signals to only a few of the available routing layers, and providing low-impedance paths for AC currents to travel between reference planes (decoupling capacitors at specific locations on the PCB).

---

**Conclusion**

This application note is an overview of the important principles of power distribution systems, followed by a step-by-step process for designing a PDS. This is an iterative method of PDS design, where the designer first creates a generic network, simulates and refines it, then measures it, and then refines it again based on the measured results is described. When this method fails to give an acceptable result, other possible contributors to the problem are explored. Through the use of this method, all PDS problems can be resolved.

**References**

Appendix A: Glossary

**Land**: A section of exposed metal on the surface of a PCB where surface-mount devices are soldered

**Network Analyzer**: An instrument used to measure the frequency-domain characteristics of electrical networks. The electrical characteristics of power distribution systems are often measured using a network analyzer.

**Oscilloscope**: An instrument used to show the time-domain voltage of a signal. Power supply noise is the signal measured when establishing the magnitude of noise voltage on a power supply.

**Sandwich**: A pair of planes in a PCB stackup separated only by dielectric material, no signal layer is in-between. In most cases, one of these planes will be at ground potential and the other plane will carry power. Also known as buried capacitance.

**Spectrum Analyzer**: An instrument used to measure the frequency content of a signal. Power supply noise is the signal measured when establishing the characteristics of a power distribution system.

**Stackup**: The series of layers in a PCB is often referred to as a stackup. Multi-layered boards are comprised of alternating layers of signal routing or plane metal and dielectric material. The dielectric material also serves as a structural substrate.

**Via**: A vertical connection in a PCB, usually formed by drilling a hole through the PCB and plating the walls of this hole with conductive material. Vias make electrical connections between different layers of a PCB. Vias can represent impedance discontinuities when they are in a signal path, and represent additional parasitic inductance when they are in a power distribution path (both are undesirable). The parasitic inductance formula is shown in Appendix B: Calculation of Via Inductance.

**Voltage Ripple**: Power supply noise is often referred to as voltage ripple. The maximum voltage ripple corresponds to the maximum amount of power supply variation allowed by a part’s absolute maximum ratings.

Appendix B: Calculation of Via Inductance

Via inductance is a major contributor to the parasitic inductance of a capacitor mounting. The dimensions of a via largely determine its parasitic inductance. Equation 5, from Grover (Reference #2), is used to determine the self-inductance of a single filled via based on its length and diameter. Dimensions are in inches and nano-Henries.

$$L = 5.08 \times h \times \left(\ln\left(\frac{4 \times h}{d}\right) - 0.75\right)$$  \hspace{0.5cm} \text{Equation 5}

**Example**

To calculate the inductance of a via going from the bottom surface of the board to the top surface of the board, use the board finished thickness for via length: the board finished thickness at 62 mils, the via diameter at 3 mils. There are 1000 mils in an inch.

\[ h = 0.062 \text{ in} \]
\[ d = 0.003 \text{ in} \]

\[ L = 5.08 \times 0.062 \times \left[ \ln\left(\frac{4 \times 0.062}{0.003}\right) - 0.75\right] \]

\[ L = 5.08 \times 0.062 \times 3.67 \]

\[ L = 1.15 \text{ nH} \]
This result is the self-inductance of a single via. The self-inductance is only one part of the total inductance of the current loop the via is a part of. Since the mutual inductance of vias with opposing currents (power and ground), will have its own effect on the total inductance, it should be taken into account when greater accuracy is desired. The mutual inductance of closely-spaced complementary vias will lower the total inductance by a small amount.

This appendix demonstrates the method used to simulate decoupling capacitor networks in SPICE. Both HSPICE and PSPICE techniques are briefly discussed here. Other variants of SPICE or dedicated PDS simulation software can also be used. The two simulations referenced below are purely for illustrative purposes. Simulator details are beyond the scope of this discussion and are left to the readers’ investigation. The HSPICE result is included in Figure 11. The PSPICE schematic representation and result has been included in Figure 12 and Figure 13.

These capacitor networks represent the capacitance and parasitics of an 18 capacitor network. The general capacitor array impedance calculation follows these steps:

1. Formulate a netlist for the L-C-R network
2. Understand where the input node and output node are located
3. Apply an AC stimulus to the input port
4. Run an AC analysis on the L-C-R network
5. Measure the input current as well as the input AC voltage
6. Formulate \( Z = \frac{V}{I} \)
7. Plot the result using a log scale for ease of viewing

In both SPICE approaches, the AC stimulus is set to 1A. The AC Analysis directive sweeps an AC current waveform across a prescribed set of frequency points. The number of frequency points per decade is commented in the appended HSPICE netlist. With the AC current magnitude set to 1A, the impedance is calculated based on \( Z = \frac{V}{I} \). Thus, \( V \) is the main calculated variable — the voltage at the capacitor array positive node. In Figure 13, the circle with the letter V points to this node.

Two other details complete the SPICE decks.

1. There is a DC bias resistor to ground
2. There is a small input resistor connecting the AC source to the L-C-R network (this is optional).

Item 1 is necessary to decrease simulation time. It allows SPICE to quickly calculate an operating point for the circuit prior to AC analysis. This is accomplished by providing SPICE a DC path to the L-C-R network (to ground by way of the bias resistor). Item 2 is optional, but convenient. It provides a component to monitor the input current to the L-C-R network.

There are two different methods for viewing the simulated impedance result. In HSPICE, the .net directive is executed in order that HSPICE calculate \( Z_{IN} \) for direct plotting. In PSPICE the graphic capabilities of PROBE (the graphical viewer in PSPICE) were used. This approach simply utilized the expression dialogue box to formulate \( Z = \frac{V}{I} \).

**HSPICE Netlist**

HSPICE Output

Figure 11 shows the HSPICE output: $Z_{in}(MAG)$ using the AWAVES graphical viewer.

Helpful HSPICE Notes

1. Remember to keep columns to 80 characters in width
2. The "**" comments out the entire line
3. The "$" comments out all statements within the line thereafter
4. Remove all special characters that may be encountered is going from DOS to UNIX or vice versa.
5. SPICE decks end with a .end statement
PSPICE Circuit

Figure 12 shows a capacitor array with corresponding parasitic inductance and resistance.

![PSPICE Circuit](image1)

Figure 12: PSPICE Circuit

PSPICE Output

Figure 13 shows PSPICE $Z=V/I$ using the PROBE graphical viewer.

![PSPICE Output](image2)

Figure 13: PSPICE Output
Appendix D: EDA tools for PDS Design and Simulation

Table 9 lists the some vendors of EDA Tools for PDS Design and Simulation.

<table>
<thead>
<tr>
<th>Tool</th>
<th>Vendor</th>
<th>Website URL</th>
</tr>
</thead>
<tbody>
<tr>
<td>Speed 2000</td>
<td>Sigrity</td>
<td><a href="http://www.sigrity.com">http://www.sigrity.com</a></td>
</tr>
<tr>
<td>UCADES3.exe</td>
<td>UltraCAD</td>
<td><a href="http://www.ultracad.com">http://www.ultracad.com</a></td>
</tr>
<tr>
<td>Spectraquest Power Integrity</td>
<td>Cadence</td>
<td><a href="http://www.cadence.com">http://www.cadence.com</a></td>
</tr>
<tr>
<td>Star HSPICE</td>
<td>Synopsys</td>
<td><a href="http://www.synopsys.com">http://www.synopsys.com</a></td>
</tr>
</tbody>
</table>

Revision History

The following table shows the revision history for this document.

<table>
<thead>
<tr>
<th>Date</th>
<th>Version</th>
<th>Revision</th>
</tr>
</thead>
<tbody>
<tr>
<td>08/08/02</td>
<td>1.0</td>
<td>Initial Xilinx release.</td>
</tr>
<tr>
<td>04/21/03</td>
<td>1.1</td>
<td>Updated for smaller file size.</td>
</tr>
<tr>
<td>06/11/03</td>
<td>1.2</td>
<td>Minor text changes for clarity.</td>
</tr>
</tbody>
</table>